

HTZ110A Series

$I_{F(AV)} = 3.5 \text{ A}$
 $V_{RRM} = 25000 \text{ V}$

High Voltage Diode Rectifier Module

LARONTROL

Electronic Devices

Type Number	Repetitive Peak	Minimum Avalanche Voltage $V_{(BR)R}$
HTZ110A25K	25000	27200
HTZ110A22K	22000	24000
HTZ110A19K	19000	20800
HTZ110A16K	16000	17600

CIRCUIT DIAGRAM

CURRENT RATINGS - AIR COOLED			
$I_{F(AV)}$	Mean forward current	Half wave resistive load $T_{amb} = 35^{\circ}\text{C}$	3.5 A
I_F	Continuous (direct) forward current	$T_{amb} = 35^{\circ}\text{C}$	4.3 A
$R_{th(j-a)}$	Thermal resistance junction to ambient		2.3 $^{\circ}\text{C/W}$
CURRENT RATINGS - OIL COOLED			
$I_{F(AV)}$	Mean forward current	Half wave resistive load $T_{oil} = 60^{\circ}\text{C}$	5.7 A
I_T	Continuous (direct) forward current	$T_{oil} = 60^{\circ}\text{C}$	7.0 A
$R_{th(j-o)}$	Thermal resistance junction to oil		0.93 $^{\circ}\text{C/W}$
SURGE RATINGS			
I^2t	I^2t for fusing	10 ms half sine $T_{vj} = 150^{\circ}\text{C}$	200 A^2sec
I_{FSM}	Surge (non-repetitive) forward current	$T_{vj} = 150^{\circ}\text{C}$	200 A
TEMPERATURE AND FREQUENCY RATINGS			
T_{vj}	Virtual junction temperature	Forward (conducting)	180 $^{\circ}\text{C}$
		Reverse (blocking)	180 $^{\circ}\text{C}$
T_{stg}	Storage temperature range		-40 to 100 $^{\circ}\text{C}$
f	Frequency range		20 to 400 Hz
CHARACTERISTICS $T_{case} = 25^{\circ}\text{C}$ unless otherwise stated			
V_{FM}	Forward voltage	At 12 Amps peak	max 18.3 V
I_{RM}	Peak reverse current	At V_{RRM} ; $T_{case} = 150^{\circ}\text{C}$	max 0.5 mA

Dimensioned Outlines	
Dimensions shown are maximum in mm	
Weight typ.: 1,55 Kg	
IXYS reserves the right to change limits, test conditions and dimensions.	

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